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Lead-free Green

DMT47M2LDVQ

DUAL 40V N-CHANNEL ENHANCEMENT MODE MOSFET
PowerDI3333-8

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_C = +25°C
40V	10.8mΩ @ V_{GS} = 10V	30.2A
	15mΩ @ V_{GS} = 4.5V	25.6A

Features

- 100% Unclamped Inductive Switching, Test in Production – Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low $R_{DS(ON)}$ – Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

Description and Applications

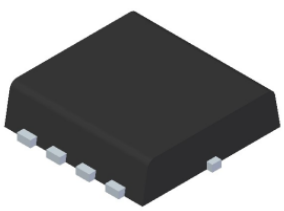
This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Motor Control
- Power Management Functions
- DC-DC Converters

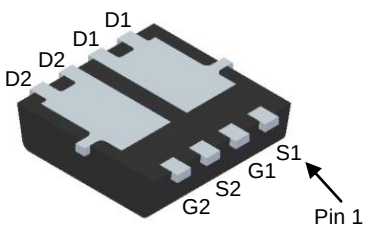
Mechanical Data

- Case: PowerDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.072 grams (Approximate)

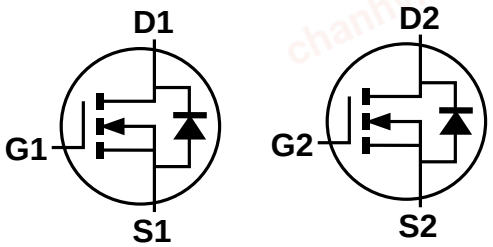
PowerDI3333-8 (Type UXC)



Top View



Bottom View



Equivalent Circuit

Ordering Information (Note 5)

Part Number	Case	Packaging
DMT47M2LDVQ-7	PowerDI3333-8 (Type UXC)	2000/Tape & Reel
DMT47M2LDVQ-13	PowerDI3333-8 (Type UXC)	3000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



M2D = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 19 for 2019)
WW = Week Code (01 to 53)

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	40	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 7), V_{GS} = 10V	T_C = +25°C T_C = +100°C	I_D	30.2 24.2	A
Continuous Drain Current (Note 6), V_{GS} = 10V	T_A = +25°C T_A = +70°C	I_D	11.9 9.5	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I_{DM}	120	A
Maximum Continuous Body Diode Forward Current (Note 7)		I_S	16.4	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		I_{SM}	120	A
Avalanche Current, L = 0.1mH (Note 8)		I_{AS}	22.1	A
Avalanche Energy, L = 0.1mH (Note 8)		E_{AS}	24.4	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	2.34	W
Thermal Resistance, Junction to Ambient (Note 6)		$R_{\theta JA}$	53.7	°C/W
Total Power Dissipation (Note 7)	T_C = +25°C	P_D	14.8	W
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	8.43	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV_{DSS}	40	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 32V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.2	1.4	2.3	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	8.4	10.8	mΩ	V_{GS} = 10V, I_D = 20A
		—	10.9	15		V_{GS} = 4.5V, I_D = 10A
Diode Forward Voltage	V_{SD}	—	0.9	1.2	V	V_{GS} = 0V, I_S = 20A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C_{iss}	—	891	—	pF	V_{DS} = 20V, V_{GS} = 0V, f = 1MHz
Output Capacitance	C_{oss}	—	490	—		
Reverse Transfer Capacitance	C_{rss}	—	14.8	—		
Gate Resistance	R_g	—	1.87	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 10V)	Q_g	—	14.0	—	nC	V_{DS} = 20V, I_D = 20A
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	6.72	—		
Gate-Source Charge	Q_{gs}	—	1.04	—		
Gate-Drain Charge	Q_{gd}	—	2.52	—		
Turn-On Delay Time	$t_{D(ON)}$	—	3.95	—	ns	V_{DD} = 20V, V_{GS} = 10V, R_G = 3Ω, I_D = 20A
Turn-On Rise Time	t_R	—	5.41	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	15.4	—		
Turn-Off Fall Time	t_F	—	8.53	—		
Body Diode Reverse Recovery Time	t_{RR}	—	56.6	—	ns	I_F = 20A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q_{RR}	—	40.0	—	nC	

Notes:
6. Device mounted on FR-4 substrate PCB, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
7. Thermal resistance from junction to soldering point (on the exposed drain pad).
8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
9. Short duration pulse test used to minimize self-heating effect.
10. Guaranteed by design. Not subject to product testing.

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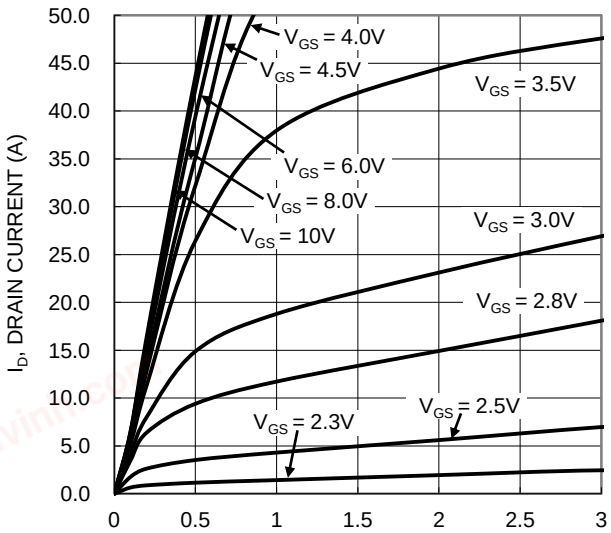


Figure 1. Typical Output Characteristic

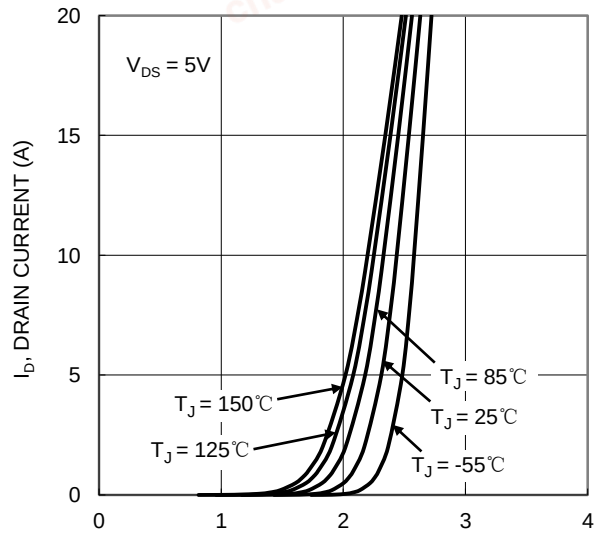


Figure 2. Typical Transfer Characteristic

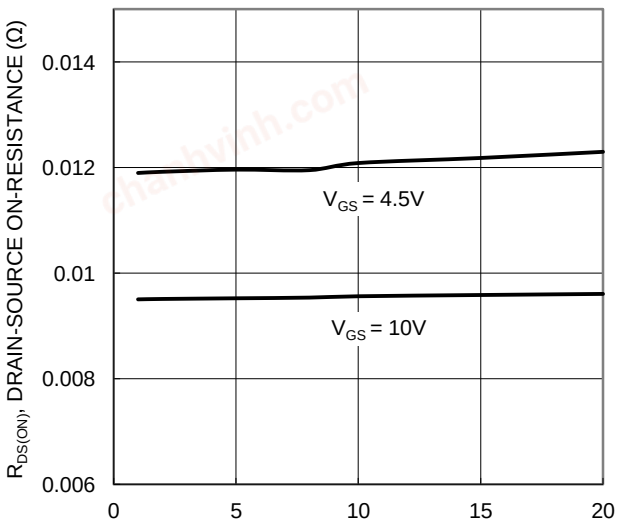


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

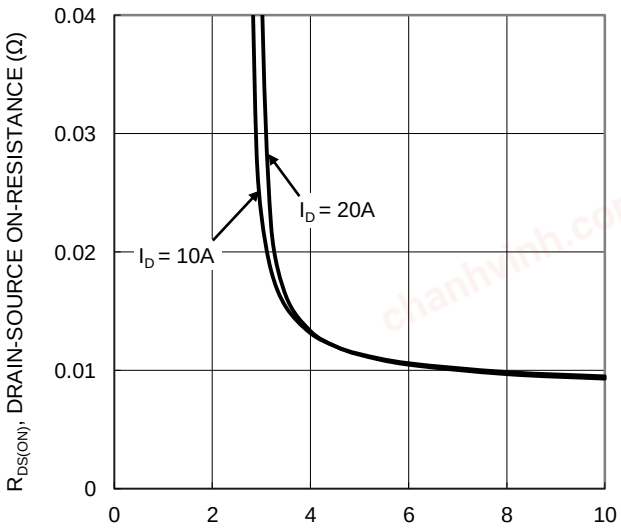


Figure 4. Typical Transfer Characteristic

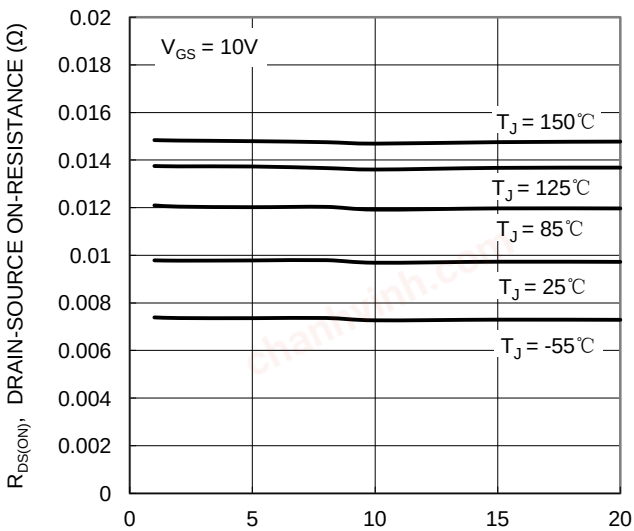


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

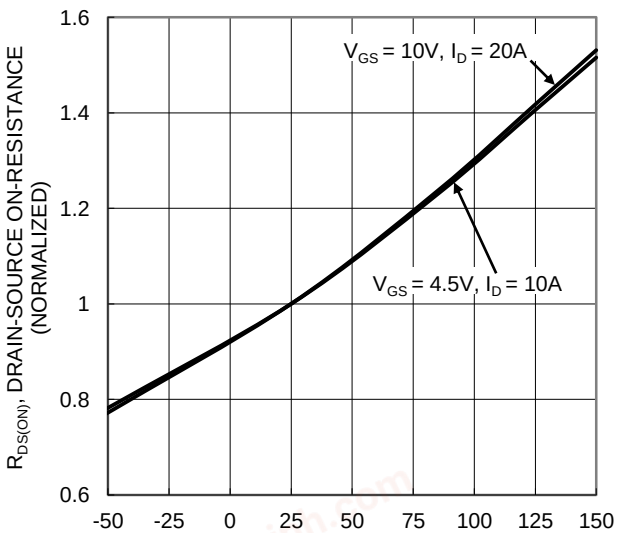


Figure 6. On-Resistance Variation with Junction Temperature

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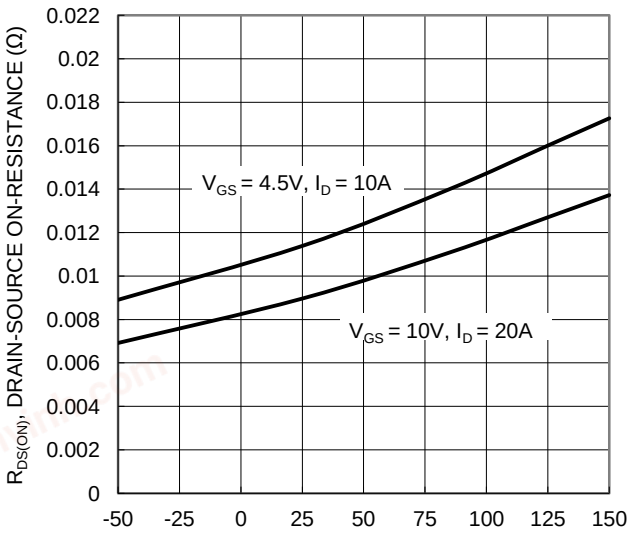


Figure 7. On-Resistance Variation with Junction Temperature

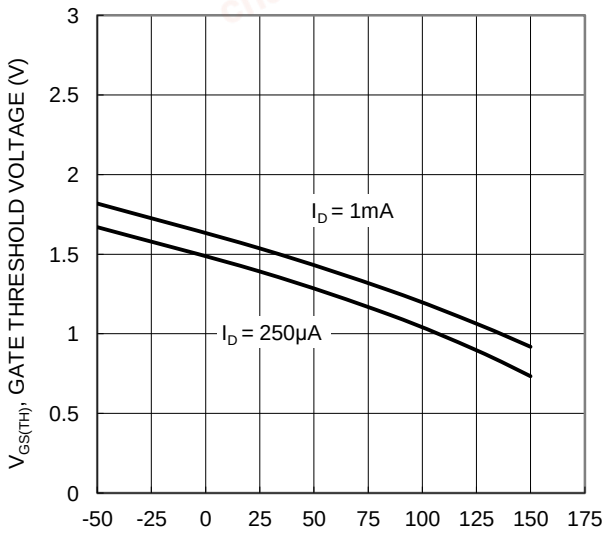


Figure 8. Gate Threshold Variation vs. Junction Temperature

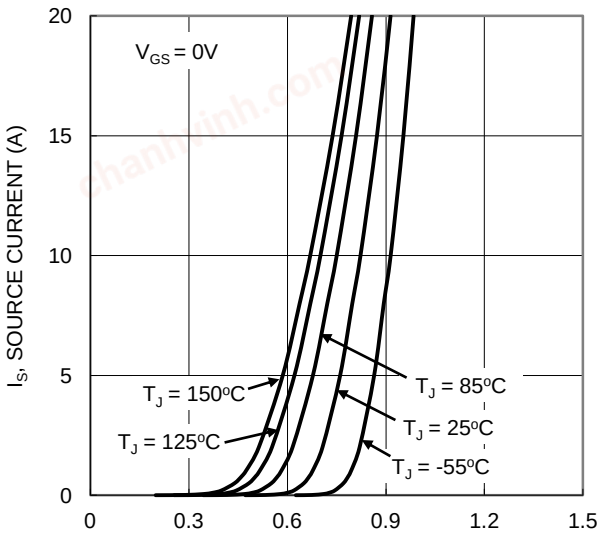


Figure 9. Diode Forward Voltage vs. Current

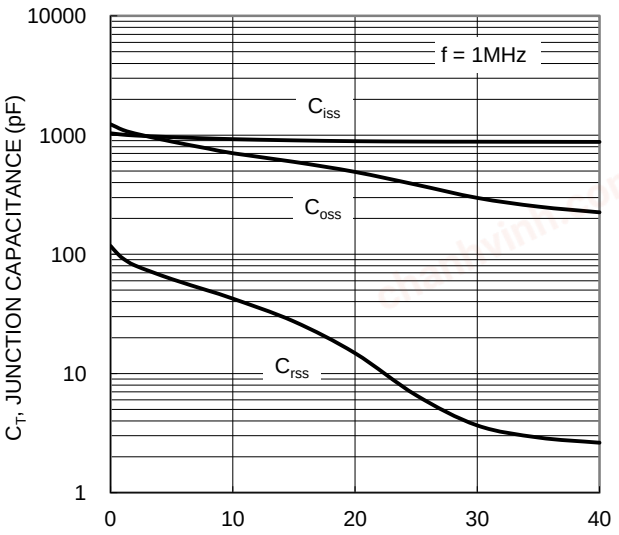


Figure 10. Typical Junction Capacitance

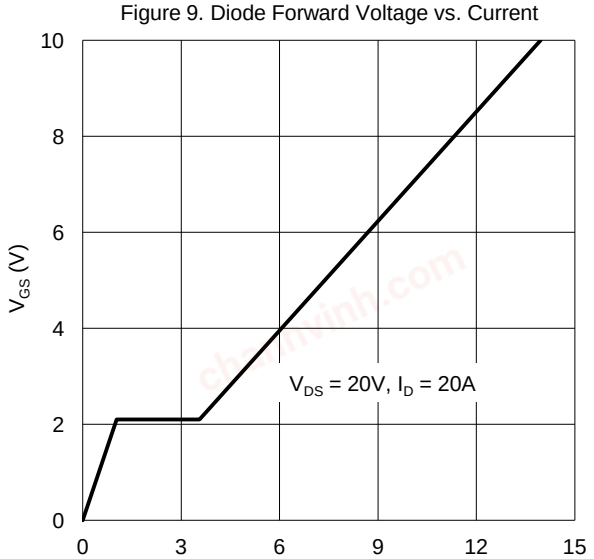


Figure 11. Gate Charge

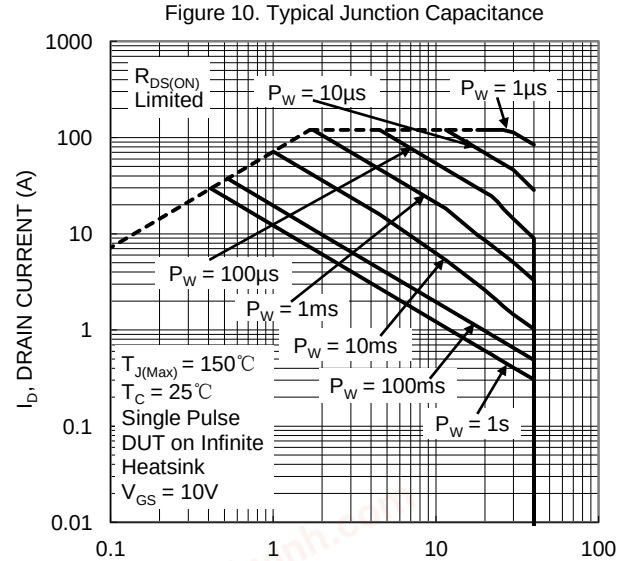


Figure 12. SOA, Safe Operation Area

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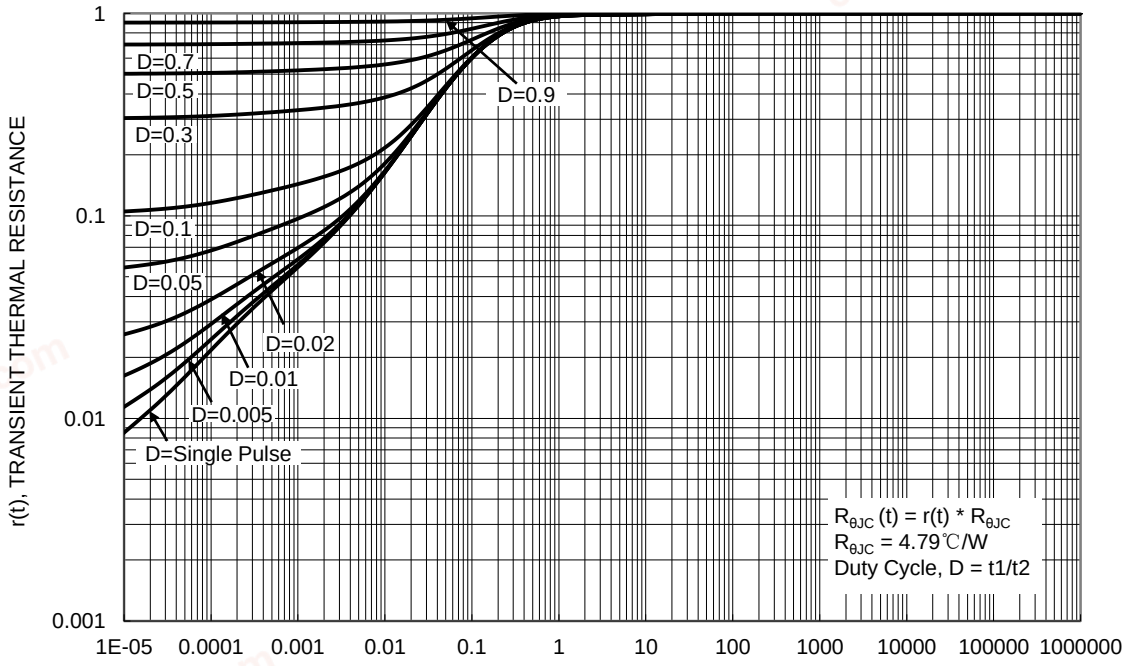


Figure 13. Transient Thermal Resistance

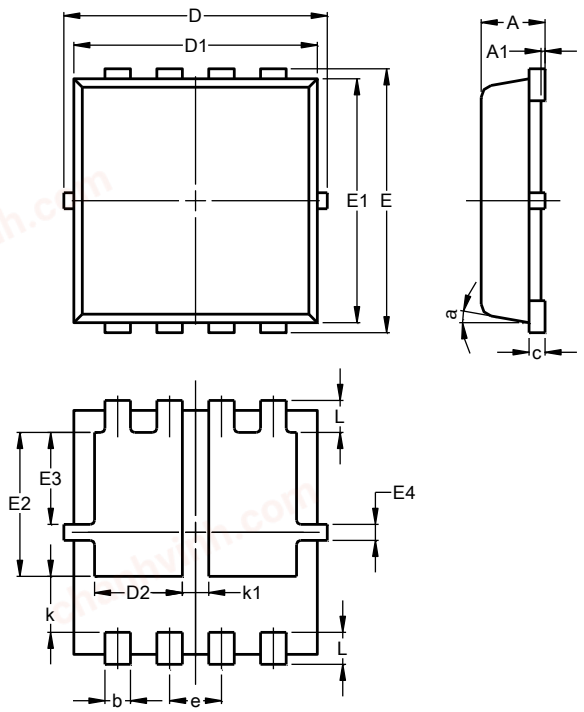
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Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UXC)

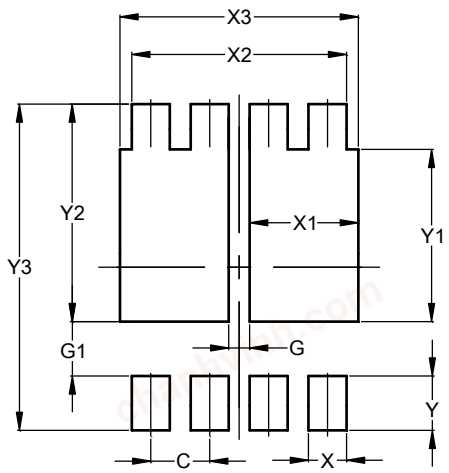


PowerDI3333-8 (Type UXC)			
Dim	**Min**	**Max**	**Typ**
A	0.75	0.85	0.80
A1	0.00	0.05	--
b	0.25	0.40	0.32
c	0.10	0.25	0.15
D	3.20	3.40	3.30
D1	2.95	3.15	3.05
D2	0.90	1.30	1.10
E	3.20	3.40	3.30
E1	2.95	3.15	3.05
E2	1.60	2.00	1.80
E3	0.95	1.35	1.15
E4	0.10	0.30	0.20
e	–	–	0.65
L	0.30	0.50	0.40
k	0.50	0.90	0.70
k1	0.13	0.53	0.33
a	0°	12°	10°
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UXC)



Dimensions	Value (in mm)
C	0.650
G	0.230
G1	0.600
X	0.420
X1	1.200
X2	2.370
X3	2.630
Y	0.600
Y1	1.900
Y2	2.400
Y3	3.600

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